

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (L^2 - π -MOSV)

2SJ508

Chopper Regulator, DC-DC Converter and Motor Drive Applications

- 4 V gate drive
- Low drain-source ON resistance : $R_{DS(ON)} = 1.35 \Omega$ (typ.)
- High forward transfer admittance : $|Y_{fs}| = 0.7 S$ (typ.)
- Low leakage current : $I_{DSS} = -100 \mu A$ ($V_{DS} = -100 V$)
- Enhancement-mode : $V_{th} = -0.8 \sim -2.0 V$ ($V_{DS} = -10 V$, $I_D = -1 mA$)

Maximum Ratings ($T_a = 25^\circ C$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-100	V
Drain-gate voltage ($R_{GS} = 20 k\Omega$)		V_{DGR}	-100	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	-1	A
	Pulse (Note 1)	I_{DP}	-3	A
Drain power dissipation		P_D	0.5	W
Drain power dissipation (Note 2)		P_D	1.5	W
Single pulse avalanche energy (Note 3)		E_{AS}	136.5	mJ
Avalanche current		I_{AR}	-1	A
Repetitive avalanche energy (Note 4)		E_{AR}	0.05	mJ
Channel temperature		T_{ch}	150	$^\circ C$
Storage temperature range		T_{stg}	-55~150	$^\circ C$

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	250	$^\circ C / W$

Note 1: Please use devices on condition that the channel temperature is below $150^\circ C$.

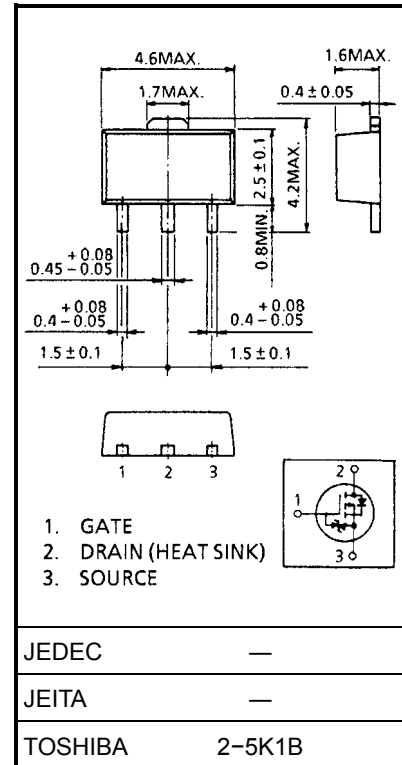
Note 2: Mounted on ceramic substrate ($25.4 mm \times 25.4 mm \times 0.8 mm$)

Note 3: $V_{DD} = -50 V$, $T_{ch} = 25^\circ C$ (initial), $L = 168 mH$, $R_G = 25 \Omega$, $I_{AR} = -1 A$

Note 4: Repetitive rating: Pulse width limited by maximum channel temperature

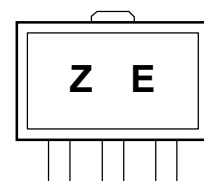
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



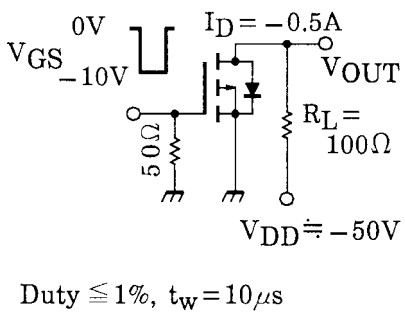
Weight: 0.05 g (typ.)

Marking



(The two digits represent the part number.)

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-off current		I_{DSS}	$V_{DS} = -100 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-100	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	—	-2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = -4 \text{ V}, I_D = -0.5 \text{ A}$	—	1.68	2.5	Ω
			$V_{GS} = -10 \text{ V}, I_D = -0.5 \text{ A}$	—	1.34	1.9	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -0.5 \text{ A}$	0.3	0.7	—	S
Input capacitance		C_{iss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	135	—	pF
Reverse transfer capacitance		C_{rss}		—	22	—	
Output capacitance		C_{oss}		—	48	—	
Switching time	Rise time	t_r	 $V_{GS} = 0 \text{ V}, -10 \text{ V}$ $I_D = -0.5 \text{ A}$ V_{OUT} $R_L = 100 \Omega$ $V_{DD} \approx -50 \text{ V}$ 50Ω $\text{Duty} \leq 1\%, t_w = 10 \mu\text{s}$	—	20	—	ns
	Turn-on time	t_{on}		—	32	—	
	Fall time	t_f		—	25	—	
	Turn-off time	t_{off}		—	130	—	
Total gate charge (Gate-source plus gate-drain)		Q_g	$V_{DD} \approx -80 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -1 \text{ A}$	—	6.3	—	nC
Gate-source charge		Q_{gs}		—	4.1	—	
Gate-drain ("miller") charge		Q_{gd}		—	2.2	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	-1	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	-3	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = -1 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.5	V
Reverse recovery time	t_{rr}	$I_{DR} = -1 \text{ A}, V_{GS} = 0 \text{ V}$	—	90	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR} / dt = 50 \text{ A} / \mu\text{s}$	—	180	—	nC

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